

Patent Abstracts of Japan

PUBLICATION NUMBER : 06045244
PUBLICATION DATE : 18-02-94

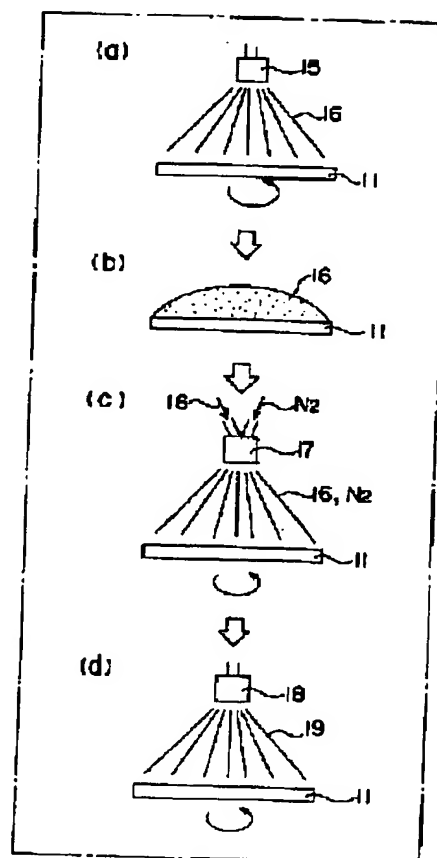
APPLICATION DATE : 30-07-91
APPLICATION NUMBER : 03214515

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INT.CL. : H01L 21/027 G03F 7/30

TITLE : DEVELOPMENT METHOD IN IC
MANUFACTURING



ABSTRACT : PURPOSE: To provide a development method used in an IC manufacturing step, in which a scum of a photoresist film remaining on a wafer is prevented in a puddle development method.

CONSTITUTION: While a wafer 11 is rotated at low speed, or put in a stationary state, a developer 16 is poured on the wafer 11, and a development step is progressing in this state. A spray of the developer 16 mixed with a gas is blown to the wafer 11 while the wafer 11 is rotated at high speed. After the development step is completed, a rinsing 19 is poured on the wafer 11 while the wafer 11 is rotated at high speed.

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